



#### 20V P-Channel Enhancement Mode MOSFET

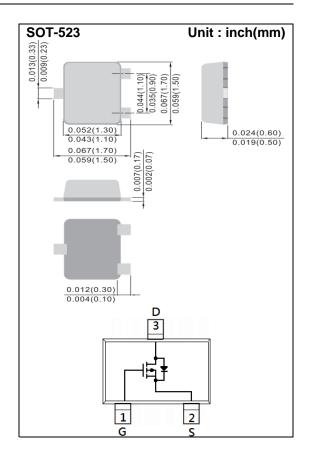
Voltage -20 V Current -0.9A

#### **Features**

- RDS(ON) , VGS@-4.5V, ID@-0.9A<130mΩ</li>
- RDS(ON) , VGS@-2.5V, ID@-0.6A<160mΩ</li>
- RDS(ON) , VGS@-1.8V, ID@-0.4A<210mΩ</li>
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

### **Mechanical Data**

- Case: SOT-523 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00007 ounces, 0.002 grams
- Marking: E01



# Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 12	V
Continuous Drain Current		I <sub>D</sub>	-0.9	Α
Pulsed Drain Current		I <sub>DM</sub>	-3.6	Α
Power Dissipation	T <sub>a</sub> =25°C	$P_{D}$	300	mW
	Derate above 25°C		2.4	mW/°C
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient (Note 3)		$R_{\theta JA}$	417	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-0.4	-0.69	-1.2	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.9A	-	110	130	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.6A	-	130	160	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-0.4A	-	160	210	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.9A, V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	5.4	-	nC
Gate-Source Charge	$Q_gs$		-	0.7	-	
Gate-Drain Charge	$Q_gd$		-	1.4	-	
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	416	-	pF
Output Capacitance	Coss		-	43	-	
Reverse Transfer Capacitance	Crss		-	32	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	\/ - 40\/ I - 0.0A	-	4	-	ns
Turn-On Rise Time	tr	$V_{DD}$ =-10V, $I_{D}$ =-0.9A, $V_{GS}$ =-4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)		27	-	
Turn-Off Delay Time	td <sub>(off)</sub>			78	-	
Turn-Off Fall Time	tf		-	45	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I <sub>S</sub>				-0.4	Α
Diode Forward Current	ış		_		-0.4	^
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.8	-1.2	V

## NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited





#### TYPICAL CHARACTERISTIC CURVES

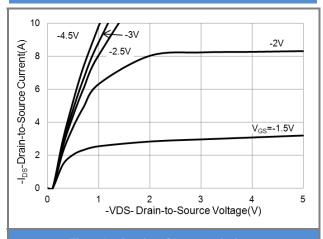
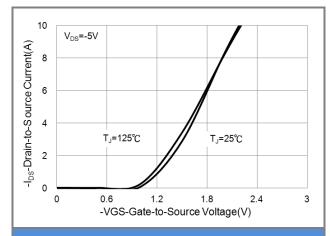


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

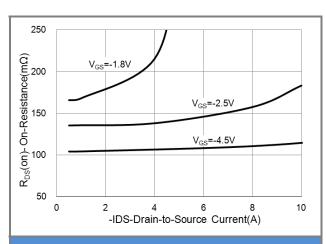


Fig.3 On-Resistance vs. Drain Current

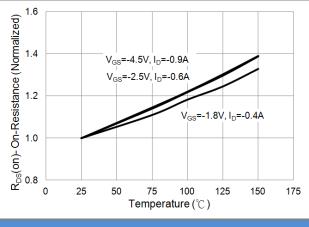
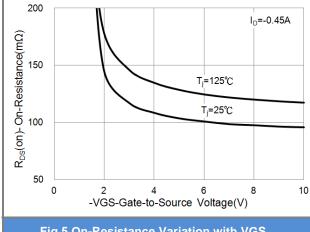
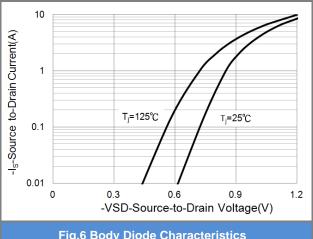


Fig.4 On-Resistance vs. Junction temperature







**Fig.6 Body Diode Characteristics** 





### **TYPICAL CHARACTERISTIC CURVES**

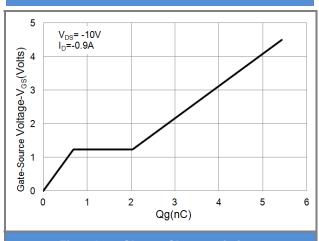


Fig.7 Gate-Charge Characteristics

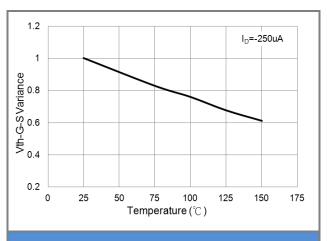


Fig.8 Threshold Voltage Variation with Temperature

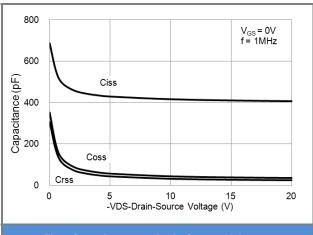


Fig.9 Capacitance vs. Drain-Source Voltage

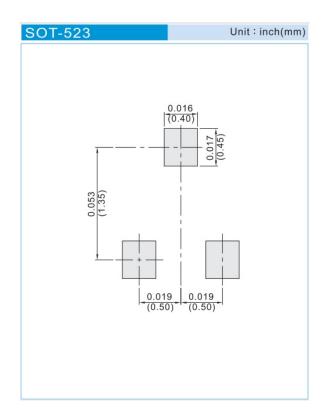




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJE8401_R1_00001	SOT-523	4K pcs / 7" reel	E01	Halogen free

## **MOUNTING PAD LAYOUT**







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